GKS005N10NF
N-Channel SGT Power MOSFE

V_{DSS}	100 V
I_D	100 A
$R_{DS(ON)}$	5.3 mΩ

Features

- Best-in-Class FOM
- Low Gate Charge
- High Current Capability

Application

- Power Management in Telecom.,Industrial Automatio
- Motor Driving in Power Tool,E-vehicle,Robotics
- Current Switching in DC/DC&AC/DC(SR) Sub-system

GK xxx
S005N10

LOGO GK xxx CODE

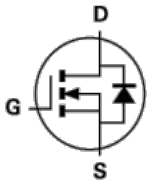
S005 N 10

$R_{DS(on)}$ VDSS

PDFN5X6-8L top&bottom view



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continue Drain Current	I_D	100	A
Pulsed Drain Current (Note1)	I_{DM}	360	A
Power Dissipation	P_D	96	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	497	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.7	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	50	°C/W

Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Electrical Characteristics (T_J=25℃unless otherwise noted)

Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{GS} = 0 V,I_D = 250 μA	BV_{DSS}	100	-	-	V
Drain-Source Leakage Current	V_{DS} = 100 V, V_{GS} = 0 V	I_{DSS}	-	-	1	μA
Gate Leakage Current	V_{GS} = ± 20 V, V_{DS} = 0 V	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	V_{DS} = V_{GS} , I_D = 250 μA	$V_{GS(th)}$	1.2	-	2.5	V
Drain-Source On-State Resistance	V_{GS} = 10 V, I_D = 20A	$R_{DS(on)}$	-	5.3	6.4	mΩ
	V_{GS} = 4.5 V, I_D = 15A	$R_{DS(on)}$	-	7.5	9.4	mΩ
Input Capacitance	VDS=50V , VGS=0V , f=1MHz	C_{iss}	-	2420	-	pF
Output Capacitance		C_{oss}	-	900	-	pF
Reverse Transfer Capacitance		C_{rss}	-	35	-	pF
Turn-on Delay Time(Note2)	VDD=50V , VGS=10V , RG=3Ω , ID=20 A	$t_{d(ON)}$	-	11.2	-	ns
Rise Time(Note2)		t_r	-	23	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	38	-	ns
Fall Time(Note2)		t_f	-	15.3	-	ns
Total Gate Charge(Note2)	VDS=50V , VGS=10V , ID=20A	Q_G	-	43	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	9.4	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	10.3	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	100	A
Drain-Source Diode Forward Voltage	VGS=0V , IS=20A , TJ=25℃	V_{SD}	-	-	1.2	V
Reverse Recovery Time(Note2)	T_J = 25℃, I_F= 20A di / dt = 100 A/μs	trr	-	42	-	ns
Reverse Recovery Charge(Note2)		Qrr	-	46	-	nC

Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

RATING AND CHARACTERISTIC CURVES

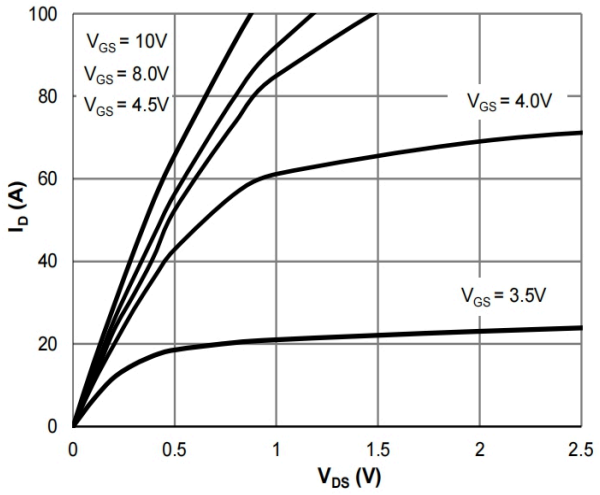


Figure 1: Saturation Characteristics

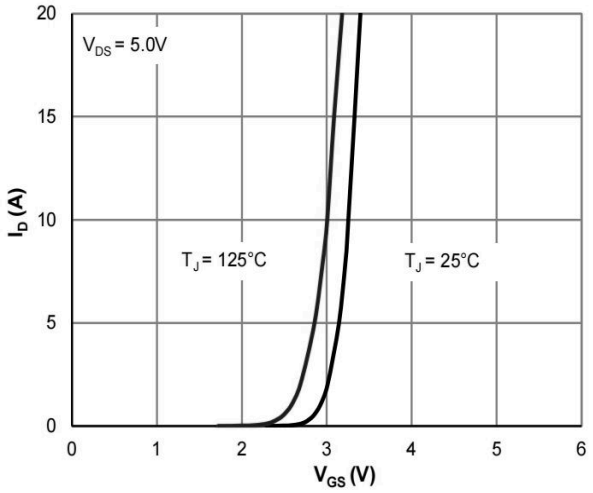


Figure 2: Transfer Characteristics

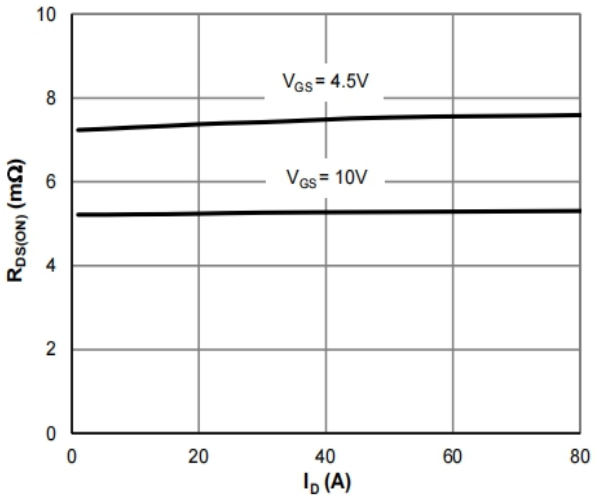


Figure 3: $R_{DS(ON)}$ vs. Drain Current

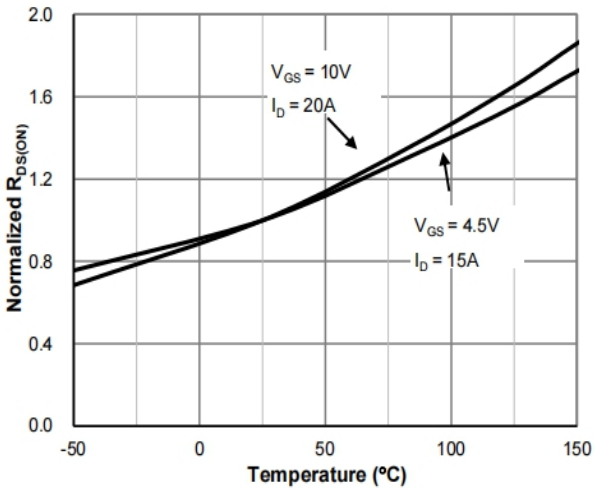


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

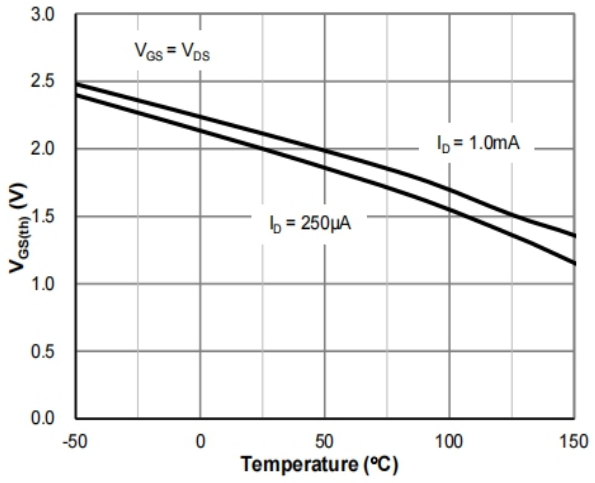


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

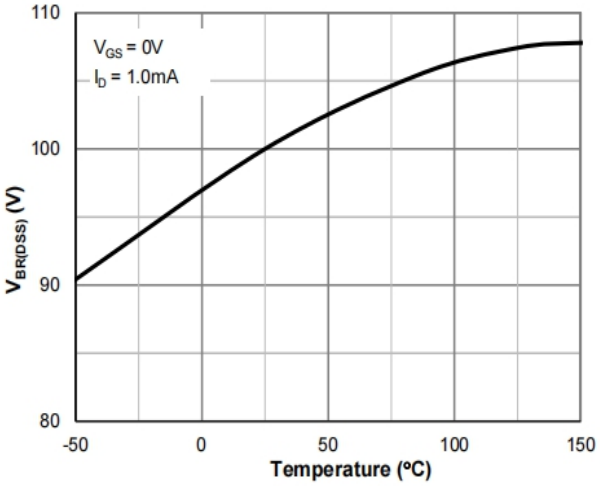


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

RATING AND CHARACTERISTIC CURVES

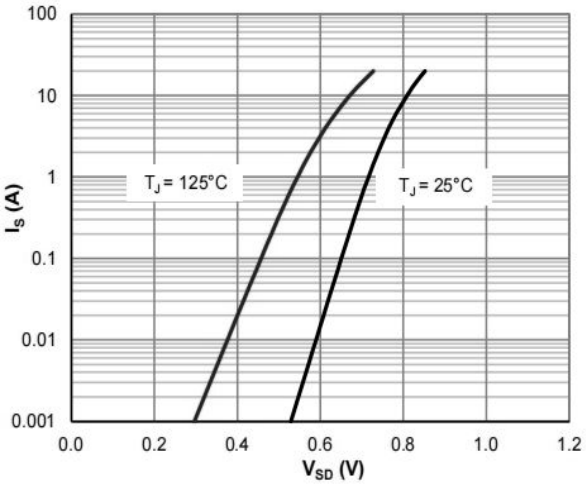


Figure 7: Body-Diode Characteristics

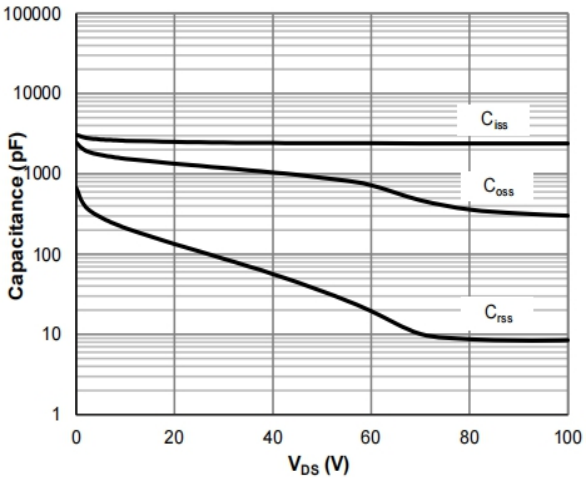


Figure 8: Capacitance Characteristics

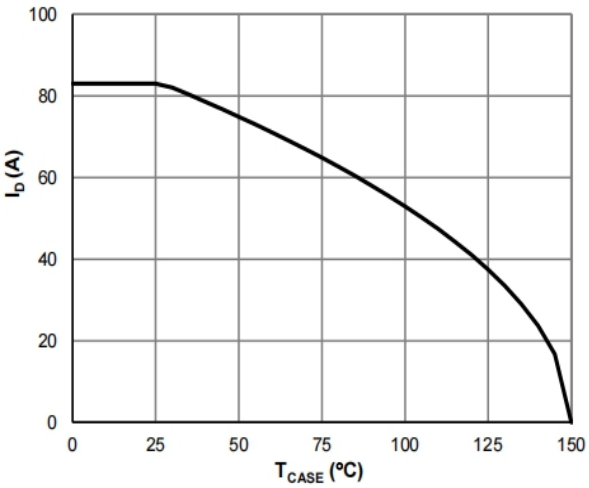


Figure 9: Current De-rating

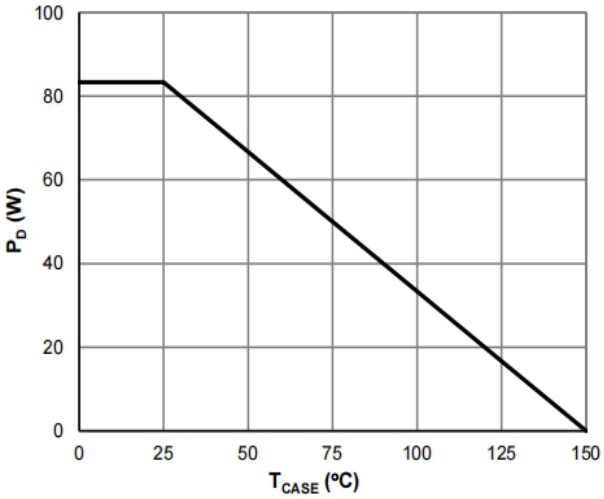


Figure 10: Power De-rating

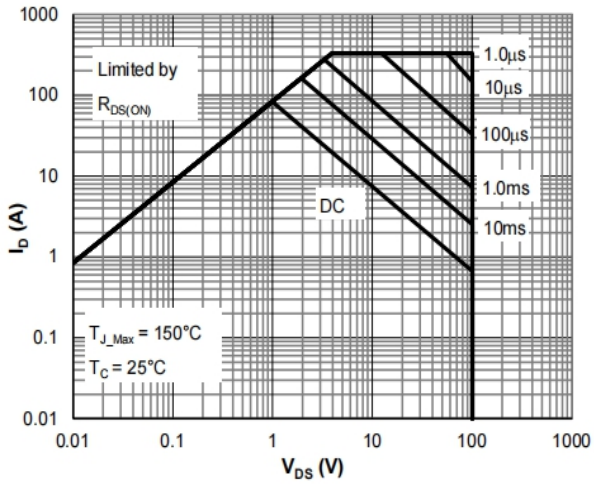


Figure 11: Maximum Safe Operating Area

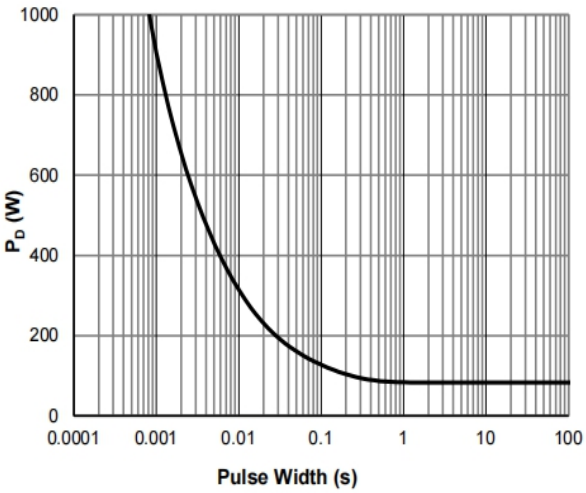
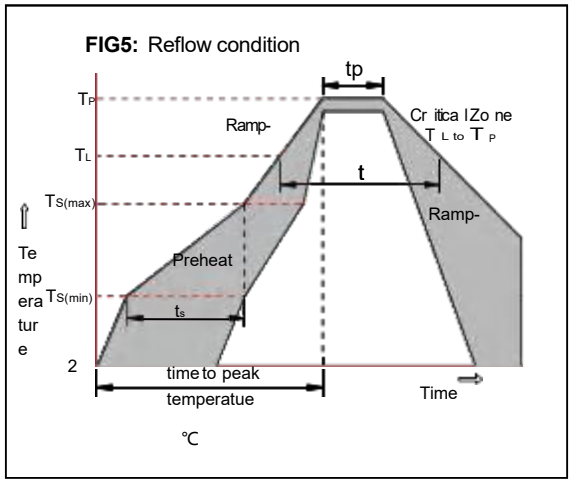


Figure 12: Single Pulse Power Rating, Junction-to-Case

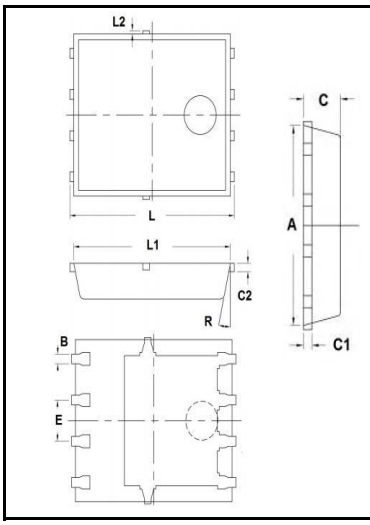
Soldering parameters

Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

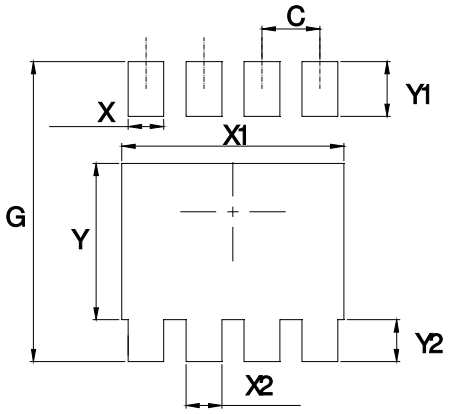


Package Dimensions & Suggested Pad Layout

PDFN5*6



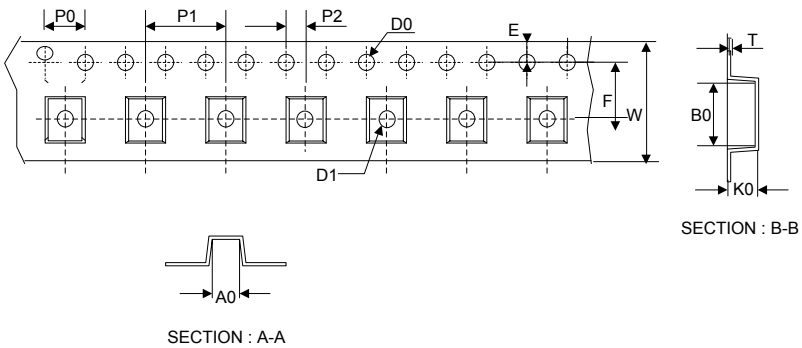
Dim.	Min.	Max.
A	4.8	5.2
B	0.25	0.35
C	1	1.2
C1	Typ0.254	
C2	Typ0.254	
E	Typ1.27	
L	6	6.3
L1	5.7	6
L2	Max0.2	
R	Typ13°	
All Dimensions in millimeter		



Dimensions	Value (in mm)
C	1.27
G	6.45
X	0.62
X1	4.50
X2	0.62
Y	3.70
Y1	1.05
Y2	0.80

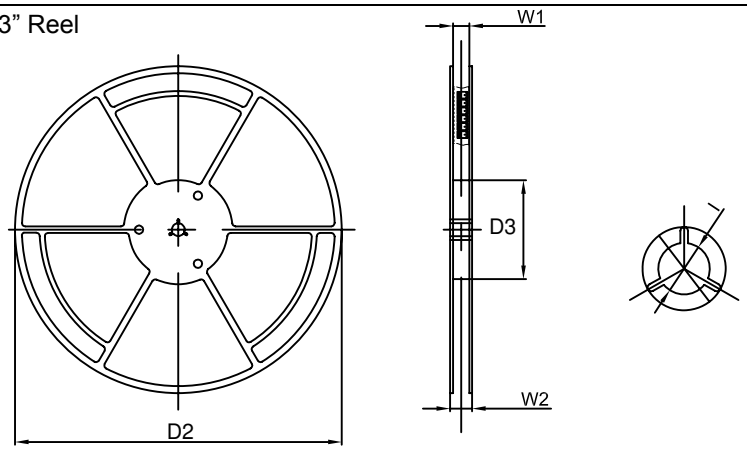
Tape & rell specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	1.55±0.20
E	1.75±0.20
F	5.50±0.20
W	12.00±0.20
A0	6.60±0.20
B0	5.70±0.20
K0	1.30±0.20
T	0.20±0.20

13” Reel



D2	330.0±5.0
D3	100.0±4.0
W1	12.0±5.0
W2	14.0±5.0
I	13.0±2.0

Quantity: 5000PCS

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